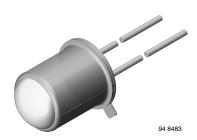
Vishay Semiconductors



Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



DESCRIPTION

TSTS7100 is an infrared, 950 nm emitting diode in GaAs technology in a hermetically sealed TO-18 package with lens.

FEATURES

Package type: leaded
Package form: TO-18
Dimensions (in mm): Ø 4.7

High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity: ϕ = ± 5°

• Peak wavelength: $\lambda_p = 950 \text{ nm}$

· Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



· Radiation source in near infrared range

| PRODUCT SUMMARY | | | | | |
|-----------------|------------------------|----------------------|-----|---------------------|--|
| COMPONENT | I _e (mW/sr) | $φ$ (deg) $λ_P$ (nm) | | t _r (ns) | |
| TSTS7100 | > 10 | ± 5 | 950 | 800 | |

Note

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | | |
|----------------------|-----------|------------------------------|--------------|--|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | | |
| TSTS7100 | Bulk | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18 | | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|-------------------------------------|---|-------------------|---------------|------|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | |
| Reverse voltage | | V _R | 5 | V | |
| Forward current | T _{case} ≤ 25 °C | I _F | 250 | mA | |
| Peak forward current | $t_p/T = 0.5, t_p \le 100 \ \mu s, T_{case} \le 25 \ ^{\circ}C$ | I _{FM} | 500 | mA | |
| Surge forward current | t _p ≤ 100 μs | I _{FSM} | 2.5 | Α | |
| Power dissipation | | Pv | 170 | mW | |
| | T _{case} ≤ 25 °C | P _V | 500 | mW | |
| Junction temperature | | T _j | 100 | °C | |
| Storage temperature range | | T _{stg} | - 55 to + 100 | °C | |
| Thermal resistance junction/ambient | leads not soldered | R _{thJA} | 450 | K/W | |
| Thermal resistance junction/case | leads not soldered | R _{thJC} | 150 | K/W | |

Note

T_{amb} = 25 °C, unless otherwise specified

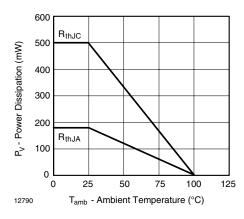








Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 950 nm, GaAs





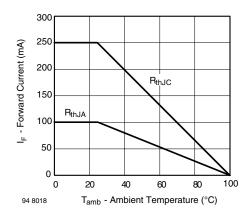


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|---|---|------------------|------|-------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$ | V_{F} | | 1.3 | 1.7 | V |
| Temperature coefficient of V _F | I _F = 100 mA | TK _{VF} | | - 1.3 | | mV/K |
| Breakdown voltage | I _R = 100 μA | $V_{(BR)}$ | 5 | | | V |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _j | | 30 | | pF |
| Radiant intensity | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | I _e | 10 | | 50 | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$ | фe | | 7 | | mW |
| Temperature coefficient of φ _e | I _F = 100 mA | TKφ _e | | - 0.8 | | %/K |
| Angle of half intensity | | φ | | ± 5 | | deg |
| Peak wavelength | I _F = 100 mA | λ_{p} | | 950 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 50 | | nm |
| Rise time | I _F = 100 mA | t _r | | 800 | | ns |
| | $I_F = 1.5 \text{ A}, t_p/T = 0.01, t_p \le 10 \mu\text{s}$ | t _r | | 400 | | ns |
| Virtual source diameter | | d | | 1.5 | | mm |

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

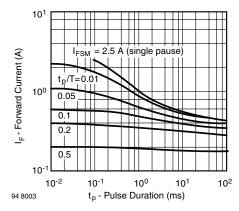


Fig. 3 - Pulse Forward Current vs. Pulse Duration

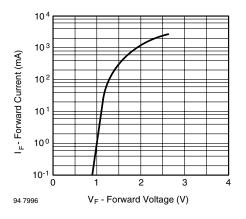


Fig. 4 - Forward Current vs. Forward Voltage

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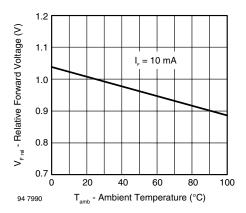


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

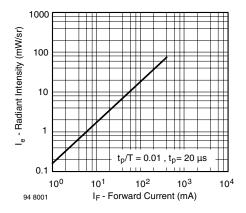


Fig. 6 - Radiant Intensity vs. Forward Current

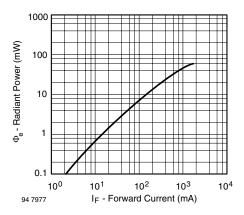


Fig. 7 - Radiant Power vs. Forward Current

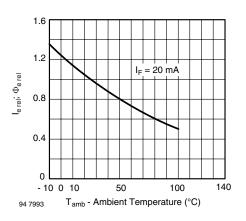


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

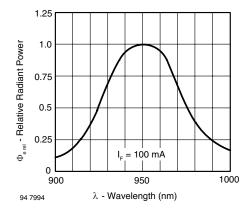


Fig. 9 - Relative Radiant Power vs. Wavelength

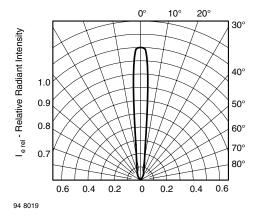
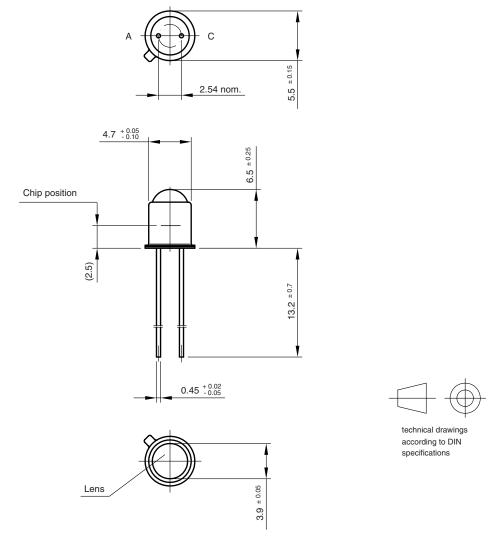


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters



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